5th International Conference on Micro-Pattern Gas Detectors (MPGD2017) and RD51 Collaboration Meeting Temple University, Philadelphia, USA May 22-26, 2017

A custom readout electronics for the BESII CGEM detector



Michela Greco

CGEM-IT group







Giulio Mezzadri' s talk

Introduction

Overview of the readout electronics for the BESIII-CGEM IT

On detector electronics

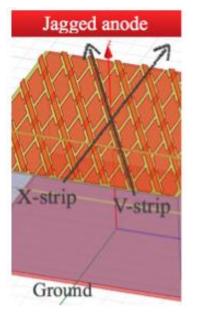
Design of a dedicated ASIC for CGEM Readout (TIGER) In silicon characterization of TIGER prototype First tests on CGEM detector

Outlook









ntroduction

Readout electronics

TIGER

In silicon

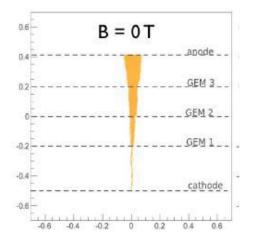
on detector

Outlook

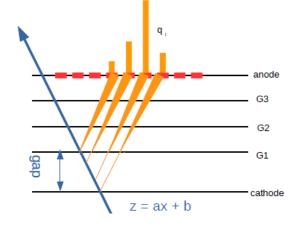
Charge centroid method

- Digital Readout
- Analog Readout
 Loosening pitch (650 µm) & less channels (about 10 thousand)

μTPC (Time Projection Chamber)



time resolution 5 ns

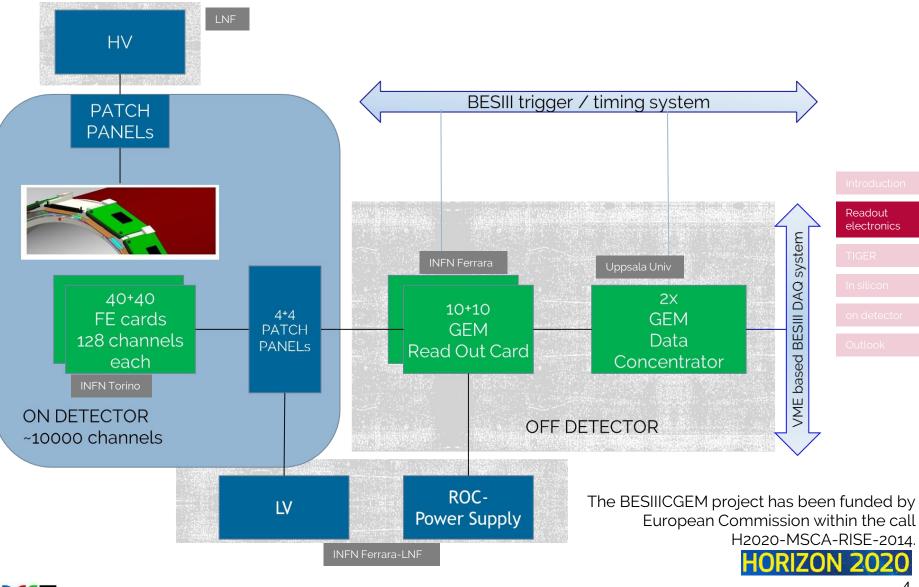


readout with 160 dedicated, integrated 64-channel ASICs



N FN'SEZIONE DI TORINO

ISTITUTO NAZIONALE DI FISICA NUCI FARE



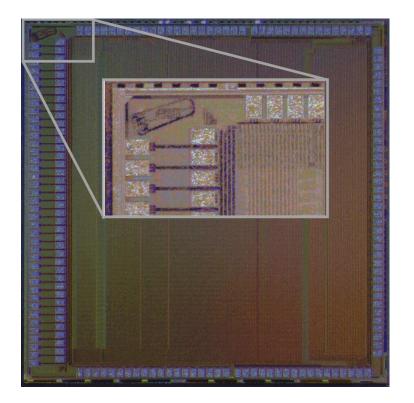
₿€SⅢ

TIGER: Torino Integrated Gem Electronics for Readout

Expected signal from CGEM-IT: 30-50 ns duration, 30-40 ns rising time, 10 ns falling time depends on gas mixture, gain and electric field

- ▶ input charge: 1 50 fC
- ▶ up to 100 pF sensor capacitance
- ▶ 4-5 ns time resolution
- 60 kHz rate per channel (safety factor of 4 included)
- ▶ power ~10 mW/channel

25 mm² UMC110 CMOS







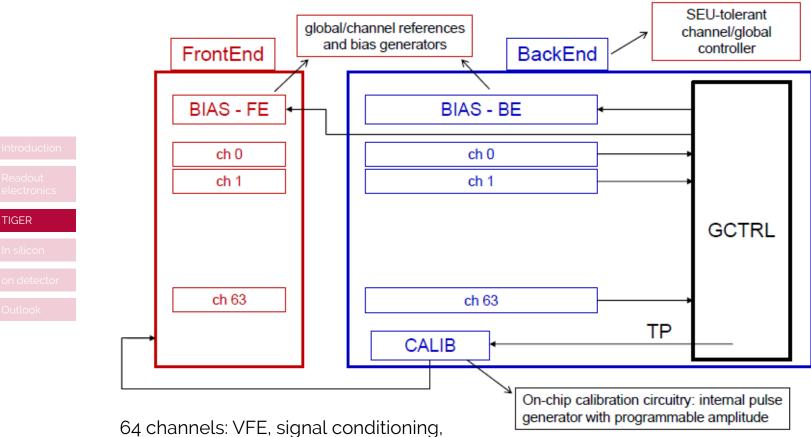
provide time and charge measurement, feature a fully-digital output be SEU-tolerant





Chip architecture





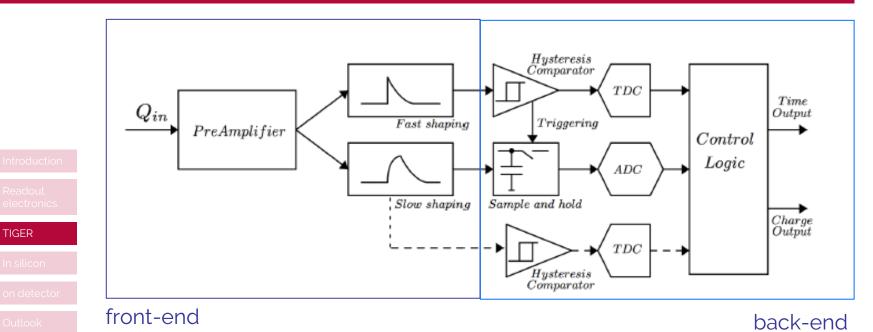
64 channels: VFE, signal conditioning, TDC/ADC, local controller on-chip bias and power management on-chip calibration circuitry fully digital output, LVDS IO 4 TX SDR/DDR links, 8B/10B encoding, 200 MHz SPI configuration link





Each channel





T-BRANCH

timestamp on rising/falling edge (sub-50 ps binning quad-buffered TDC) charge measurement with Time-over-Threshold

E-BRANCH

timestamp on rising edge (sub-50 ps binning quad-buffered TDC) Sample-and-Hold circuit for peak amplitude sampling slow shaper output voltage is sampled and digitised with a 10-bit Wilkinson ADC



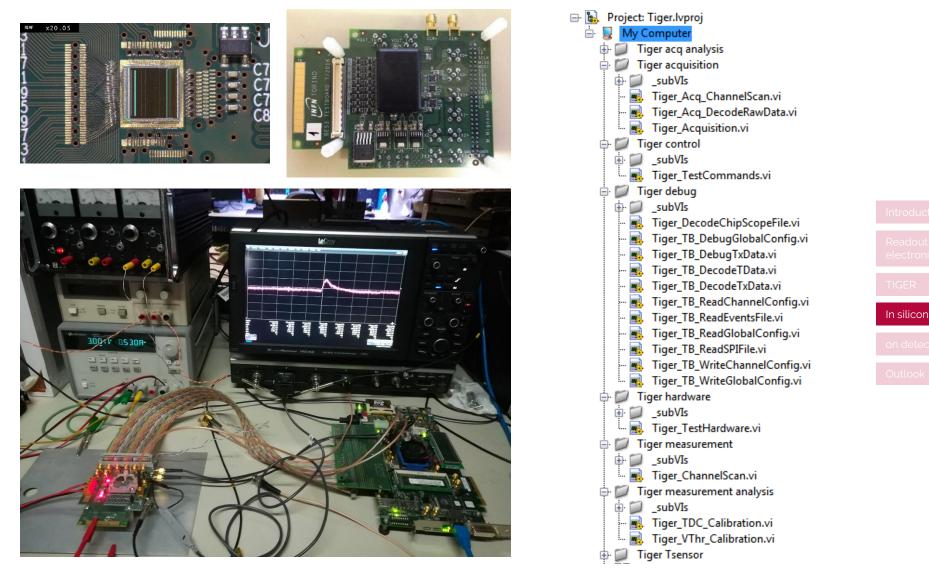
M. Greco, MPGD2017, 23 May 2017



+SEU protection

Test setup











- ✓ R/W Channel/Global configuration registers
- ✓ Data TX and decoding
- $\checkmark\,$ Baseline and threshold equalisation

(dual-) TDC operation

Front-end performance

internal calibration circuitry external charge injection (channel 63)

unexpected amplifier baseline shift, may limit linearity of Sample and Hold

→operation at higher temperature to recover BL shift



In silicon

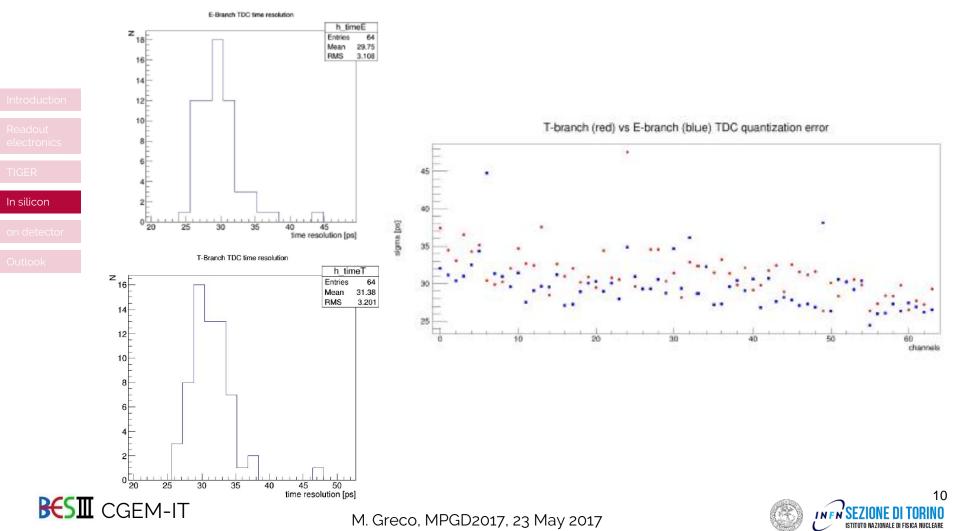


TDC operation: quantization error

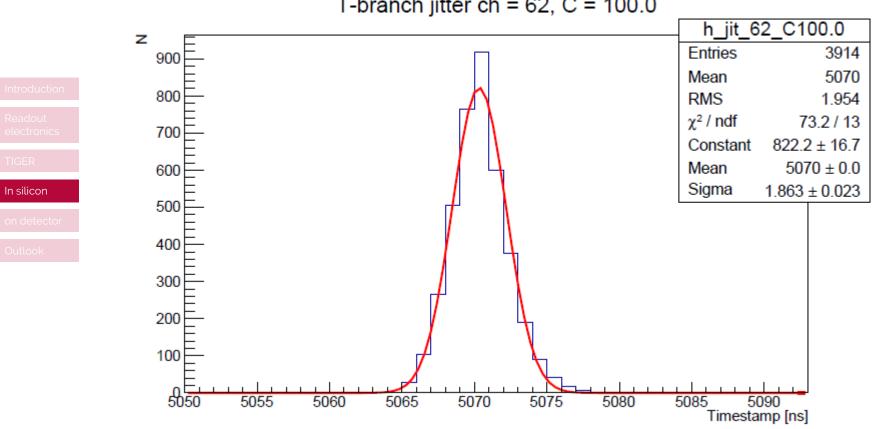


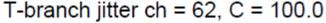
Scan over dynamic range sweeping internal test-pulse phase Create LUT with gain and offset correction

 \Rightarrow Average TDC quantization error after calibration: 30-35 ps r.m.s.



Jitter measurements using internal calibration circuit test-pulse (e.g. 10 fC) sweeping input capacitance on channel 62



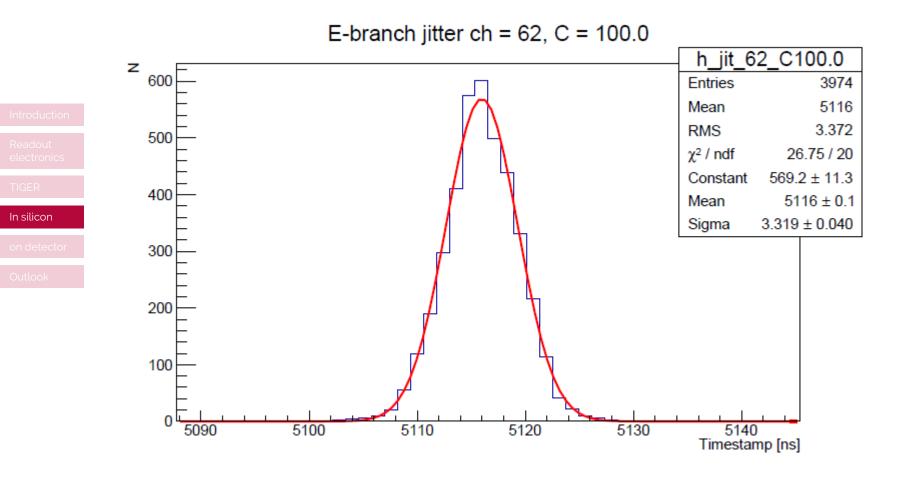




11



Jitter measurements using internal calibration circuit test-pulse (e.g. 10 fC) sweeping input capacitance on channel 62



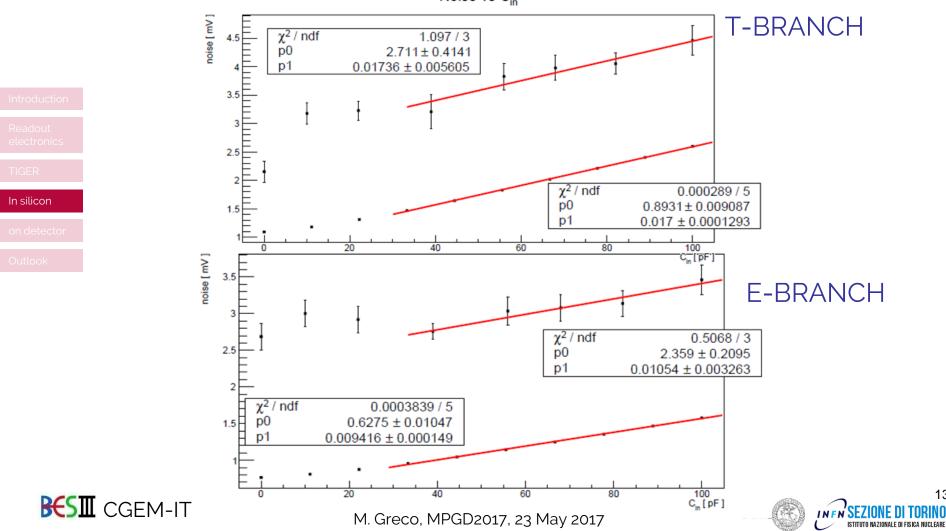






13

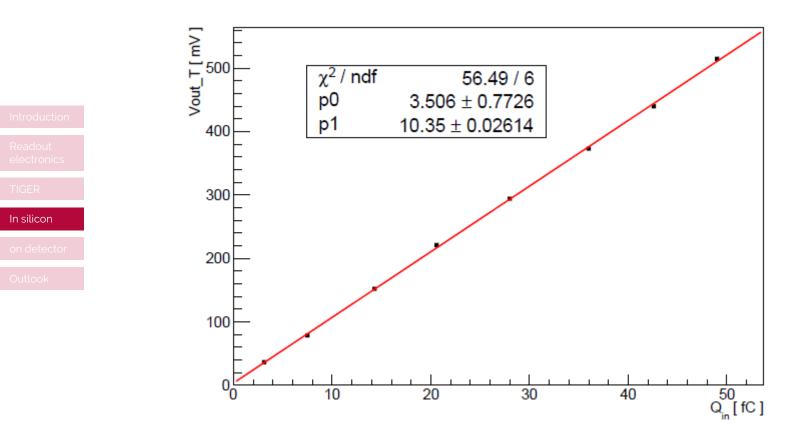
Noise evaluated for each input capacitance through a sigmoid fit from a typ 500 points threshold-scan with fixed test-pulse (10 fC) Measure repeated typ 50 times Noise vs Cin







Evaluated on channel 63 using an external pulse generator Gain: 10.4 mV/fC in agreement with simulations (expected ~11 mV/fC)



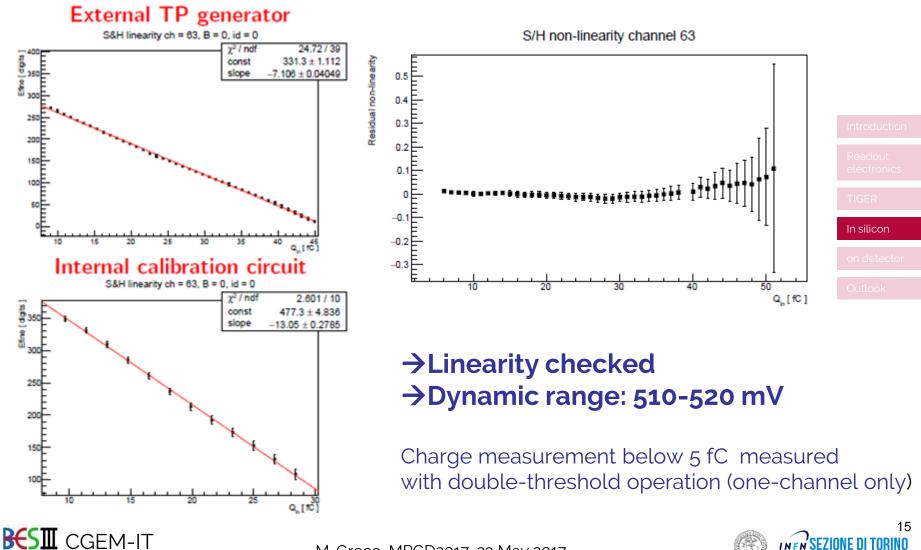




Charge measurements: Sample and Hold



Calibration of dynamic range with external test-pulse generator Back-annotation to generate a parameter space for the internal calibration circuit





Time-based readout working properly

Baseline dependence on temperature

root cause: fragility of bias conditions of baseline holder circuit reproduced fairly well in simulations minor revision activities started

Charge measurement: S/H linearity assessed

Main result: no second prototype needed

→GEM testing

to assess the performance as it explores a realistic grounding and noise pick-up environment.

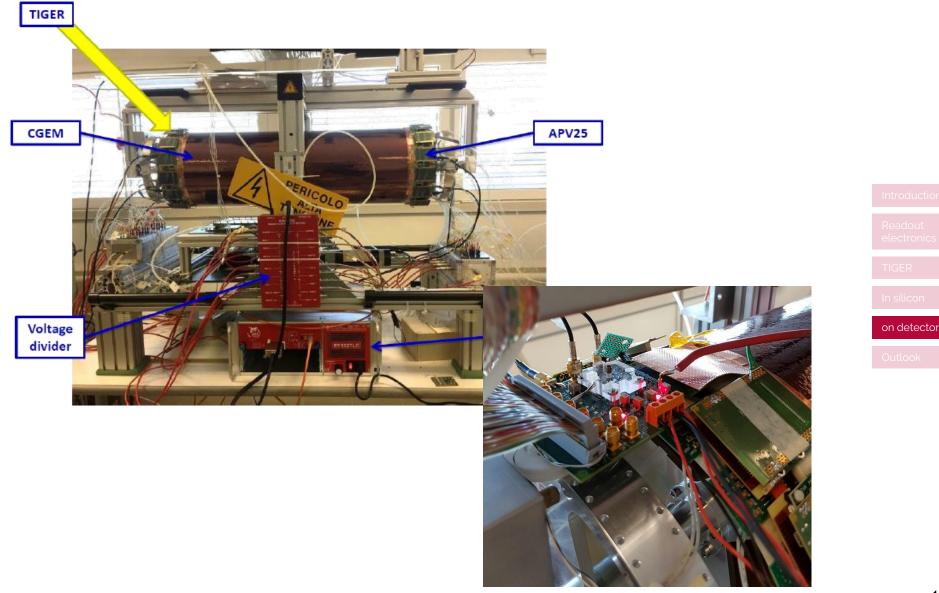






GEM testing





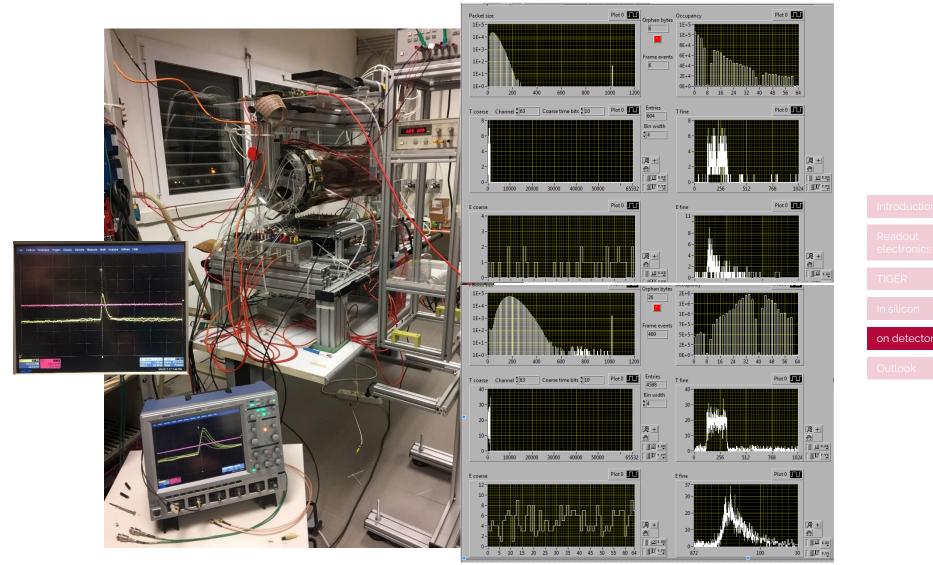




GEM testing

₩CGEM-IT

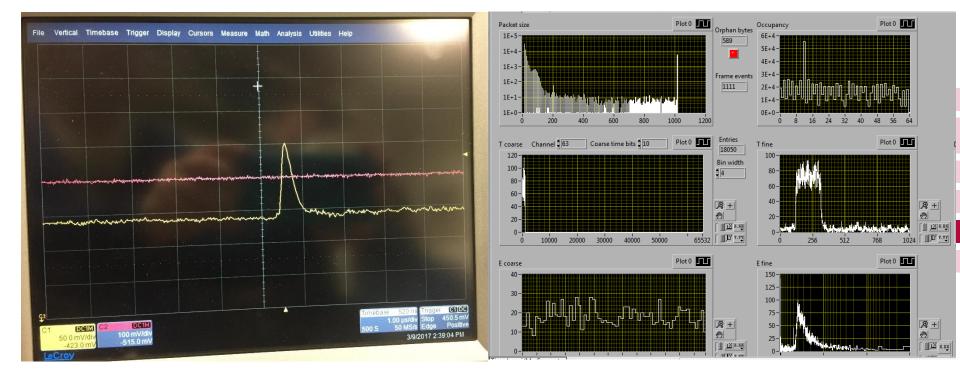




First signals with 90-Sr source







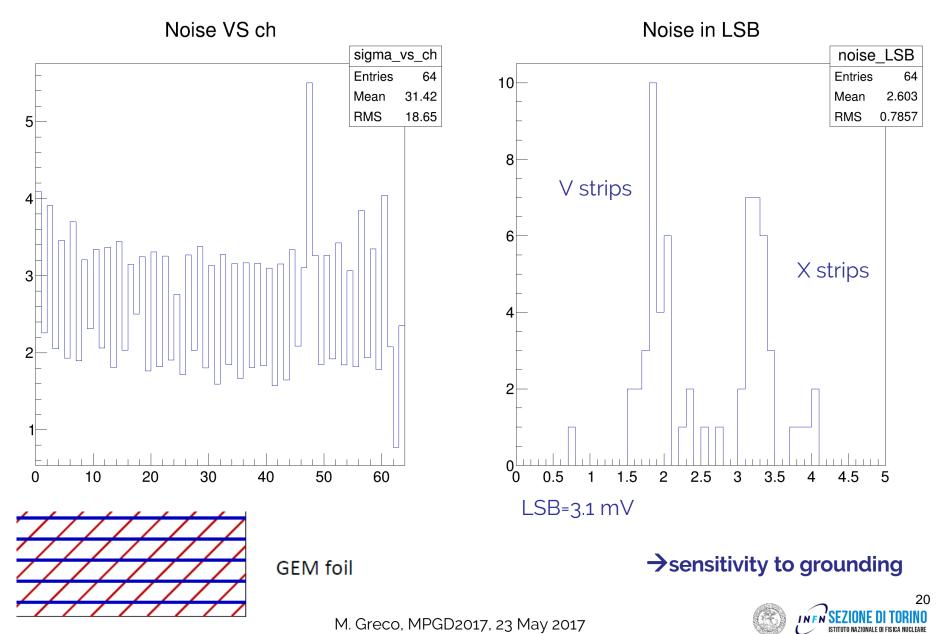
First signals with cosmic rays (night acquisition)





Noise







Test board irradiated to about 30 krad to test radiation damage on Voltage Regulators

Analog power: TPS78601KTTT_TPS78601DCO



Digital power:				2	
	PRE (V)	POST (V)	%		-07/08
Analog power					-0.7/0.8
T1	1,23	2 1,222	0,992	2	ok!
T2	1,23	2 1,222	0,992	2	
Digital power					
Тз	1,23	2 1,222	0,992	2	
Τ4	2,50	5 2,488	0,993	3	
	LT3021]	
for	Voltage refe	erence			
	PRE (V)	POST (V)	%		
Vref (T5)	0,835	0,867	1,038	3	
Vblh (T7)	0,301	0,327	1,086	6	we wi
Vout_th	0,575	0,452	0,786	6	resistor volt
Vout_y	0,506	0,5	0,988	3	



SEU test \rightarrow run at Legnaro Sirad facility Higher dose TID test on planning







TIGER, in silicon electrical characterization

main result! a second prototype is not needed, minor revisions in engineering run (summer 2017)

First tests with cylindrical GEM & first signals acquired!

S/H dynamic range, noise under study
data analysis ongoing
→test with conditions more similar to final ones,
in terms of HV distribution system, FE cards, etc.

Radiation hardness tests:

Good results from first tests on voltage regulators SEU and other TID tests on planning





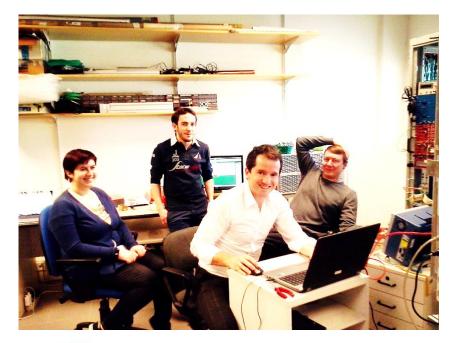


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The BESIIICGEM project has been funded by European Commission within the call H2020-MSCA-RISE-2014.





Torino TIGER WG

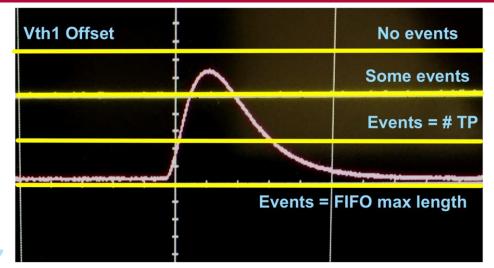
Fabio Cossio, Marco Mignone, Angelo Rivetti Manuel Rolo, Richard Wheadon Maxim Alexeev, Martina Gertosio Michela Greco, Simonetta Marcello

Thank-You

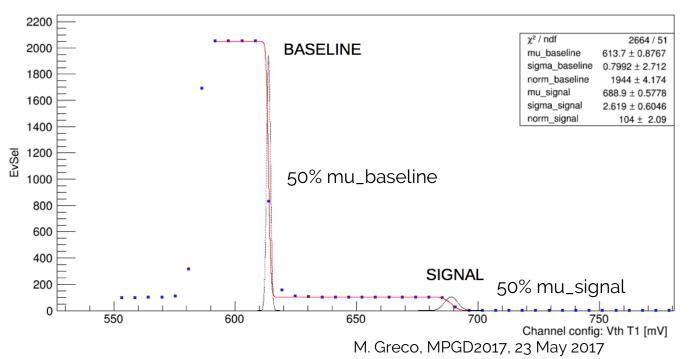


Baseline scan





events_selected_ch63



Introduction

Readout

TIGER

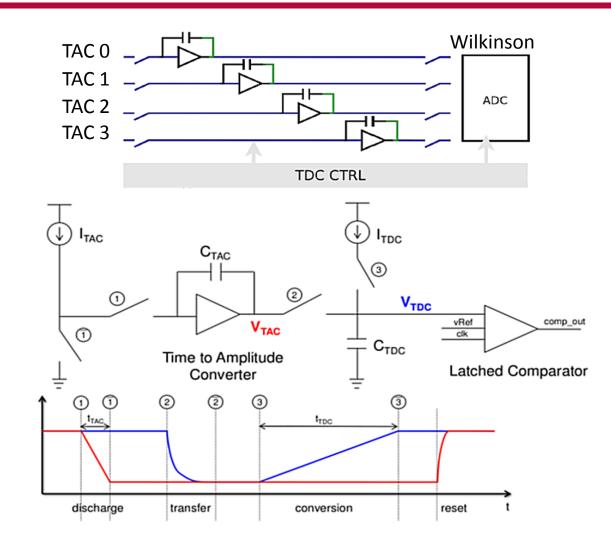
In silicon

on detecto

Dutlook







Both TAC and S/H circuits employ a quad-buffer scheme to de-randomize the input event rate and lessen the issue of the inherently high conversion time of this approach.

K28.1	10	channel 6 bit	tac	T_coarse 16 bit	E_coarse 10 bit	T_fine 10 bit	E_fine 10 bit
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